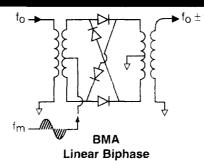
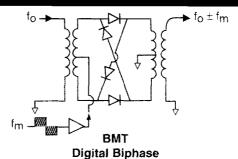
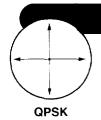
BPSK

BIPHASE MODULATORS AND UPCONVERTERS

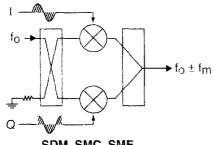


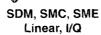


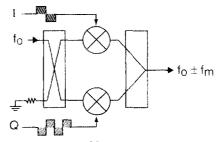
	FREQUENCY RANGE		CARRIER DRIVEN		MODULATION DRIVEN (LINEAR RF BPSK)				
			(NOTE 1) CARRIER SIDEBAND		(NOTE 2) PHASE/AMP		CARRIER		
MODEL	RE	1	REJECTION	HARMONICS	ERROR (Max.)	STATIC LOSS/P 1 (IB	REJECTION		
NUMBER	(GHz)	:GHz;	(dBc)	(dBc)	(±deg -±dB)	(dB. Max) (dBm)	(dBc. Typ.)	OUTLINES	NOTES
EMTERIZENCTO SMANKOZIAZ	0.65 - 1.75 0.5 - 2	TTL DC 0.5	NA SE	NA ga	3/03 3/03	5/+45 5/+5	30 30	ili m	Privacies
	n Wester College		20 S B S S S S S		SAN CONTENT A PARAMETER CONTENTS	ROLLED INPL		dari vina	
	Charles and the Charles and th		35 30	. 30 35	3/03	4/+5		30	Hermetic
	The Part of the Control of the Contr								
BMA0104LW2	1-4	DC -1	30 94	30			35	33	Hermetic
	1-4 2-8 2-18	DC - 2 DC - 0.5	25	30 20	5/0.5 10/0.75	4.7+5 5/+5	. 35 35 20	33 31	Low 1/f Schottle Low 1/f Schottle
BMA0104LW2 BMA0208LW2	2-8	DC-2	25	30 20 N/A	5/0.5	47+5	25		Low 1/1 Schottle
BMA0104LW2 BMA0206LW2 BMA0218LA1	2 – 8 2 – 18	DC -2 DC -0.5	25 15	30 20	5 / 0.5 10 / 0.75	4.7+5 57+5	35 20	333 1	Low 1/1 Schottk Low 1/1 Schottk



QPSK AND QAM MODULATORS





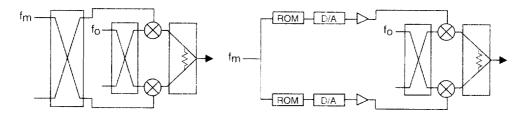


SMT Digital, Linear RF

	FREDUENO	°V BANGI	CARRIER DRIVEN LINEAR IF QAM (NOTE 1) CARRIER SIDEBAND		MODULATION DRIVEN (LINEAR RF OPSK) (NOTE 2) PHASE/AMP		CARRIER		
MODEL	RF	H.	REJECTION	HARMONICS	ERROR (Max.)	STATIC LOSS/P 1 dB	REJECTION		
NUMBER	(GHz)	(GH2)	(dBc)	(dBc)	(±deg./±dB)	(dB, Max.) / (dBm)	(dBc. Typ.)	DUTLINES	NOTES
			L	NEAR I/	Q OR RF I	NPUTS			
	05-2	DC - 0.5	25	29	7/075	7/48	33		
MT0502LC1	0.5 - 2	TIL	N/A	N/A	10/1.5	7/48	35	10	
M2737LI6Q	2.7 - 3.7	DC - 0.5	30 30	25 28 25	5/0.5	7/+8	35 35	25	- 8
DM0104LC1Q	1-4	DC-0.5		23	7 / 0.75		34	8 21	The state of
SOMOSO7LI1Q	3.4 - 6.4	DC - 0.3	30		5/0.5	7/+6	95		8
SMC0208LI1Q	1.5 - 6.5	DC - 0.5	30	25	7 / 0.75	10 / +16	35	21	8
SDM0607Ll3Q	6 – 7	DC - 0.5	30	25	5 / 0.5	7 / +5	35	24	8
SDM6474LQ	6.4 - 7.4	DC - 0.1	30	25	N/A	N/A	35	26	
ME0208LI1Q	2 – 8	DC - 0.5	20	30	7.5 / 0.75	10 / +6	25	21	8
DM0708LI3Q	7.2 - 8.4	DC - 0.3	30	25	5 / 0.5	8 / +5	35	24	8
ML0711LMBQ	7 – 11	DC - 0.5	50	24 25	N/A	N/A	N/A ·	27	LO = 1/2 R
DM1015LIGQ	10 - 15	DC-1	30		7 / 0.75	9/+8	38	27 24 20	8
MT0218LC1	2-18	TTL	. N/A	N/A	15/1.5	9/+3	. 20	. 20	Park Malaka
MC0618L11Q	6-18	DC 0.5	30	25	12 / 1.25		33 30	21	8
ME0618LHQ	6-18	DC - 0.03	20	30	10/1.0	10/+16	30	21	. 8

SSB UPCONVERTERS AND VECTOR MODULATORS/PHASE SHIFTERS





SDM, SML-A...D Single-Sideband Upconverter LO and 1/2 LO

SMC, SME...AVC/DIQ Analog/Digital, Phase/Amp Control

FREQUENC				RIFOAM) TE1≀	(LINEAR BE PM) (NOTE 2)				
	R∤		CARRIER	SIDEBAND	CARRIER	SIDEBAND	CONVERSION		
	IN AND OUT	GHz	REJECTION	REJECTION	REJECTION	REJECTION	LOSS		
NUMBER	(GHz)	(Note 3)	(dBc)	(dBc)	(dBc)	. Typ : (Min.)	(Typ./Max⊣	OUTLINES	NOTES
				RTERS W		NAL IF H	IYBRIDS		
EMOSOTECT"	0.5 - 1	DC - 0.5	25	18	139	25 / 15	8/10	8	
DM0502LC1	0.5 - 2	DC-0.5	25	18	39	25/15	8/10	. 8 . 8	
SDM0102LC1	1-2	DC - 0.5	25	20	35	25 / 15	8/10	. 8	
OMO104LC1	1-4	DC - 0.5	- 30	20	34	25 / 15	8/10	8	
ME0104LI1	7.1 +4	DC - 0.5	30	30	35	35 / 27	10/12	22	8
DM0204LC1	2 – 4	DC - 0.5	30	20	35	20 / 18	8 / 10	8	
M0208LC2	2 – 8	DC - 0.5	20	20	25	20 / 18	9/11	13	
ME0208LI1	2 – 8	DC - 0.5	20	30	25	35 / 27	11 / 13	22	8
MC0208LI1	2 – 8	DC - 0.5	30	25	35	25 / 23	7 / 10	21	
M0408LC2	4 – 8	DC - 0.5	25	24	30	24 / 20	6/9	13	
M0812LC2	8 – 12	DC = 0.5	25 12	23 18	30	23 / 20	6/9	13	Company of the State of the Sta
M0218LC1	2 - 18	DC-0.5		TANK DESCRIPTION OF THE PARTY O	25	18/15	9.5/11	9	
M0618LC2	6 - 18	DC - 0.5	12	18	25	20 / 18	8/9	13	
ME0618HI1	6-18	DC - 0.5	N/A	N/A	25	28 / 25	10/13	22	PIN diodes, 8
ME0618L11	6-18	DC-0.5	20	28	25	28 / 25	10/13		Schottley diodes, 8
ML0618LC2	6-18	DC-1	40	23	N/A	NA	NA		LO = 1/2 RF
M1218LC2 M0226LC1	12 - 18	DC - 1	15	15	20	23 / 20	7/9	13	
	2 – 26	DC - 0.5	15	15	20	18 /15	12 / 15	9	
ANA	ALOG OR	DIGITAL	LY CONT	ROLLED V	ECTOR M	ODULATO	DRS/PHAS	E SHIF	TERS
ME0618LI1AVC	6 – 18	DC01	N/A	N/A	30	30 / 25	12 / 15	*	Analog phase/vect
SME0618LI1DIQ	6 - 18	TTL	N/A	N/A	30	30 / 25	10 / 13	*	Digital phase/vecto

Contact factory for outline drawings

GENERAL

All modulators and SSB upconverters require that at least one of the input frequency bands (carrier or modulation) has sufficient power to turn on the semiconductors used in the various designs (i.e., Schottky diodes or PIN diodes). All modulators yield a frequency spectrum that utilizes both sidebands on either side of the output suppressed carrier. SSB upconverters employ an internal IF 90 degree hybrid to yield only 1 RF sideband output. This is offset above or below the input LO by the IF frequency (test data is recorded for the upper sideband only). Schottky diode (standard) modulators have the greatest speed and bandwidths, but yield RF output powers of typically less than 0 dBm. PIN diode (optional) designs can only be driven at modulation rates of less than 30 MHz, but will yield output RF powers exceeding +5 dBm. PIN or Schottky modulators that vary only the RF carrier phase, in many discrete steps or continuously, are referred to as phase shifters or frequency translators respectively. When output RF amplitude and phase control is required, the device is usually called a vector modulator. For the latter device, phase accuracy is usually specified over a given amplitude range (in dB). All MITEQ modulators can be driven in the carrier or modulation modes as explained below, but test data is only recorded in the modulation driven mode.

SECTION 3 NOTES

- Carrier driven: LO = +13 dBm, I/Q = 0 dBm. Used when any amplitude variation or pulse shape of the modulation must be accurately Note 1: transferred to the RF output envelope. A communication example would be directly modulating a microwave carrier with Gaussian shaped I/Q digital pulses to minimize the channel bandwidth required.
- Modulation driven: RF = 0 dBm, I/Q = +10 dBm or ±10 mA or TTL. Used when RF input has wide dynamic range, such as for military and Note 2: commercial Doppler frequency shift generation or corrections. If desired, the harmonic distortion of the relatively fixed and higher level I/Q drive third order harmonics can be linearized by "resistance/diode" or digital "ROM" wave shaping techniques. The latter is often used in vector modulator applications, such as in the model SME0618LI1DIQ design
- Note 3: To specify the IF frequency for SSB upconverter usage, select from the following standard options and add to end of model number of contact MITEQ:
 - Suffix A: 20-40 MHz, Suffix B: 40-80 MHz, Suffix C: 100-200 MHz, Suffix D: 500-1000 MHz, Suffix Q: I/Q inputs
- Note 4 Conversion loss (CL) is relative to lowest power input (f_0, f_m) . All other outputs (including f_0 , are relative to the desired upper $(f_0 + f_m)$ output Note 5: Standard units with IF hybrids are aligned for upper sideband operation. For lower sideband or selectable sideband, contact MITEQ.
- Last two characters in model number indicate standard outline number, see outline section Note 6:
- Note 7 Question and answer modulator application notes available, contact factory
- Note 8 Hermetically sealed housing.